



THE DATASHEET OF NTLUS4C12NTAG



NTLUS4C12N

MOSFET – Power, Single, N-Channel, μ Cool, UDFN6, 2.0x2.0x0.55 mm 30 V, 10.7 A



ON Semiconductor®

www.onsemi.com

Features

- Low Profile UDFN 2.0 x 2.0 x 0.55 mm for Board Space Saving with Exposed Drain Pads for Excellent Thermal Conduction
- Ultra Low $R_{DS(on)}$ to Reduce Conduction Losses
- Optimized Gate Charge to Reduce Switching Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Load Switch
- Synch DC-DC Converters
- Wireless Charging Circuit

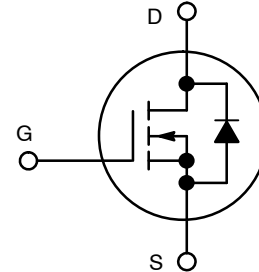
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	10.7	A
			$T_A = 85^\circ\text{C}$	7.7	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	15.1		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.54	W
			$t \leq 5$ s	$T_A = 25^\circ\text{C}$	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	6.8	A
		$T_A = 85^\circ\text{C}$	4.9		
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	P_D	0.63	W
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	I_{DM}	43	A
MOSFET Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode) (Note 1)		I_S	1.55	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

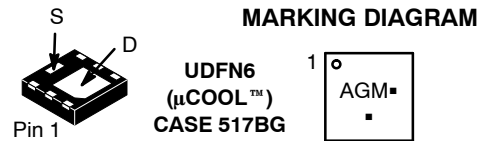
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

MOSFET		
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	9 m Ω @ 10 V	10.7 A
	12 m Ω @ 4.5 V	
	15 m Ω @ 3.7 V	
	19 m Ω @ 3.3 V	



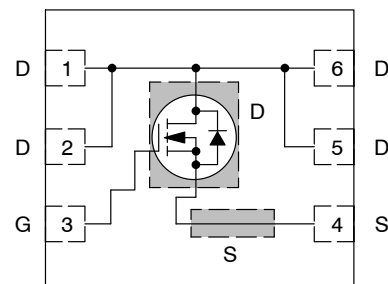
N-CHANNEL MOSFET



AG = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTLUS4C12N

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	81	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	40.5	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	200	

- Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
- Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		12		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$			1.0	μA
		$T_J = 25^\circ\text{C}$				
		$T_J = 125^\circ\text{C}$			10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.3		2.1	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			4.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 9.0\text{ A}$		7.2	9	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 8.0\text{ A}$		9.3	12	
		$V_{GS} = 3.7\text{ V}, I_D = 5.0\text{ A}$		10.9	15	
		$V_{GS} = 3.3\text{ V}, I_D = 5.0\text{ A}$		13	19	
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 9.0\text{ A}$		39		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		1172		pF
Output Capacitance	C_{OSS}			546		
Reverse Transfer Capacitance	C_{RSS}			26		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 8.0\text{ A}$		8.4		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.1		
Gate-to-Source Charge	Q_{GS}			3.0		
Gate-to-Drain Charge	Q_{GD}			2.2		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 9.0\text{ A}$		18		nC

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 15\text{ V}, I_D = 8.0\text{ A}, R_G = 3\ \Omega$		9.4		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			14		
Fall Time	t_f			3.5		

SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DD} = 15\text{ V}, I_D = 9.0\text{ A}, R_G = 3\ \Omega$		6.3		ns
Rise Time	t_r			14		
Turn-Off Delay Time	$t_{d(OFF)}$			18		
Fall Time	t_f			2.4		

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

NTLUS4C12N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 1.5\text{ A}$	$T_J = 25^\circ\text{C}$	0.72	1.1	V
			$T_J = 125^\circ\text{C}$	0.52		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V},$ $dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 1.5\text{ A}$		29		ns
Charge Time	t_a			14.1		
Discharge Time	t_b			14.9		
Reverse Recovery Charge	Q_{RR}			20		

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

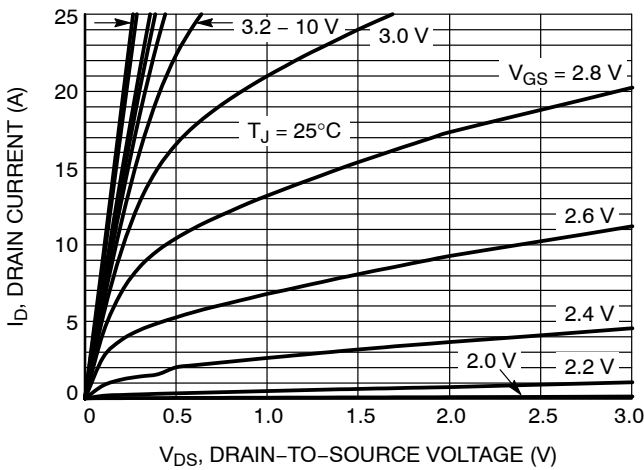


Figure 1. On-Region Characteristics

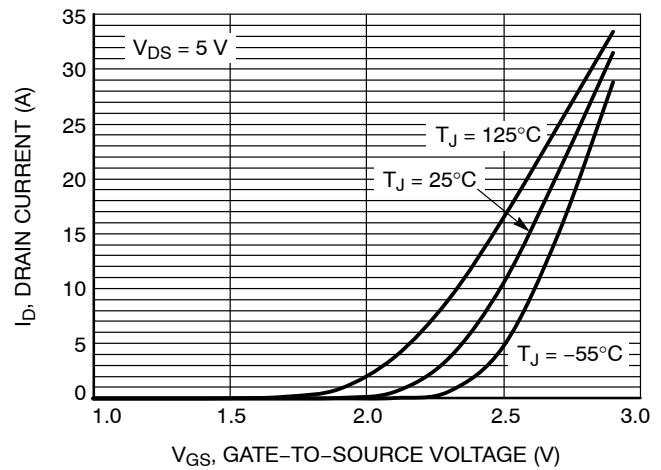


Figure 2. Transfer Characteristics

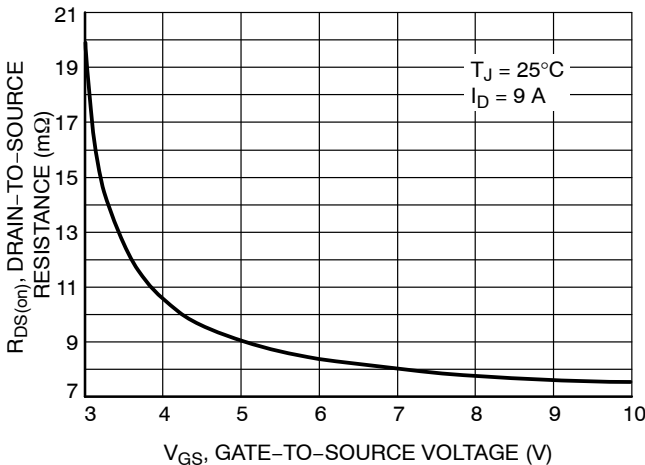


Figure 3. On-Resistance vs. Gate-to-Source Voltage

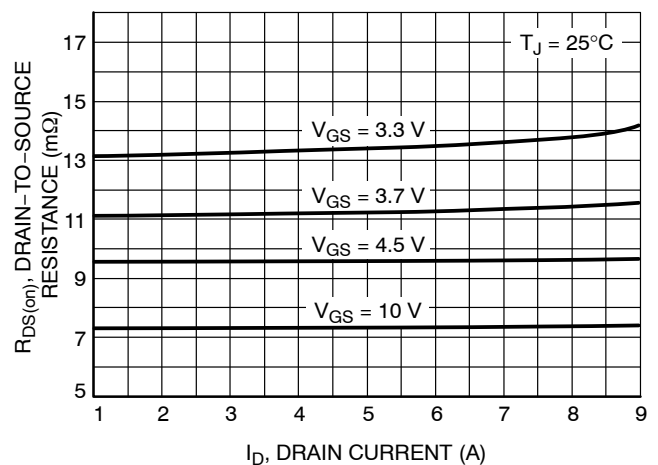


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

NTLUS4C12N

TYPICAL CHARACTERISTICS

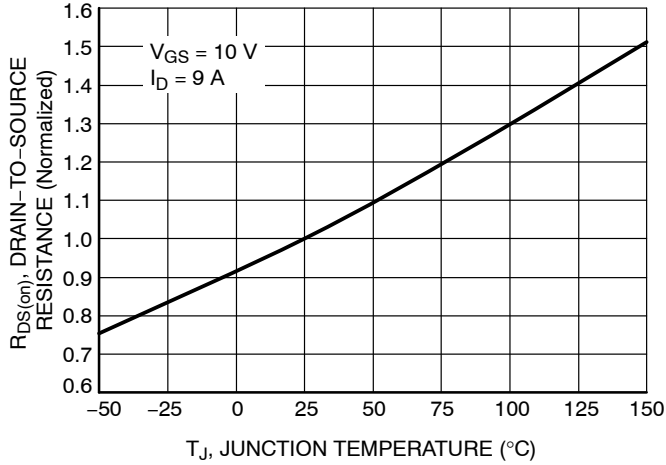


Figure 5. On-Resistance Variation with Temperature

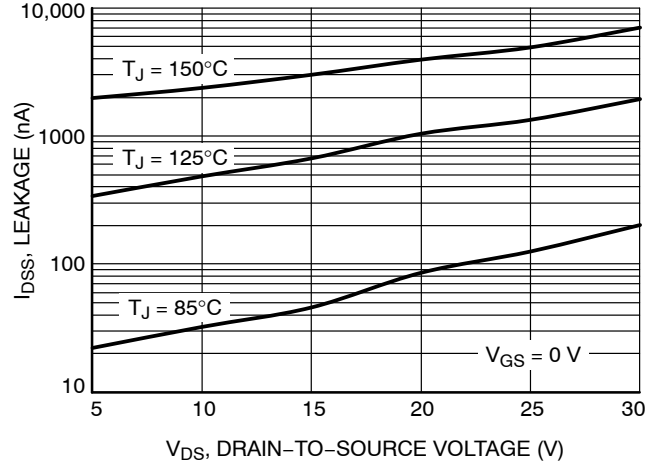


Figure 6. Drain-to-Source Leakage Current vs. Voltage

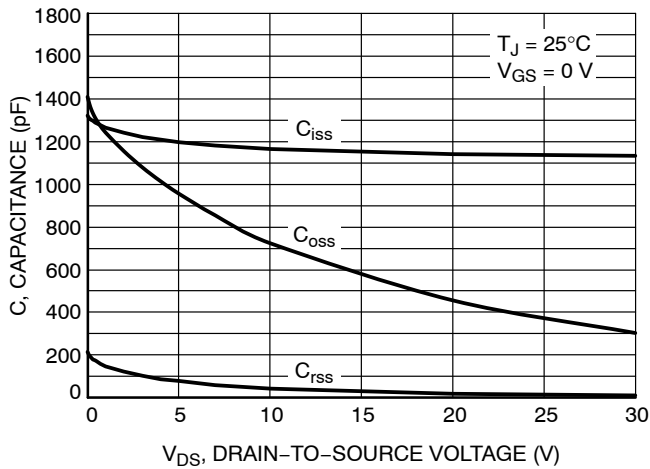


Figure 7. Capacitance Variation

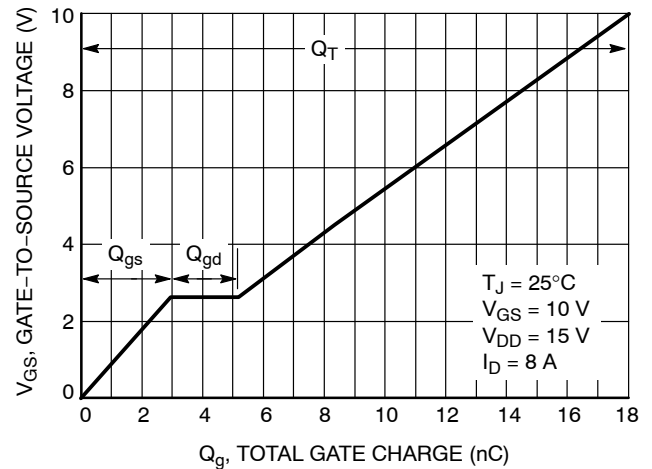


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

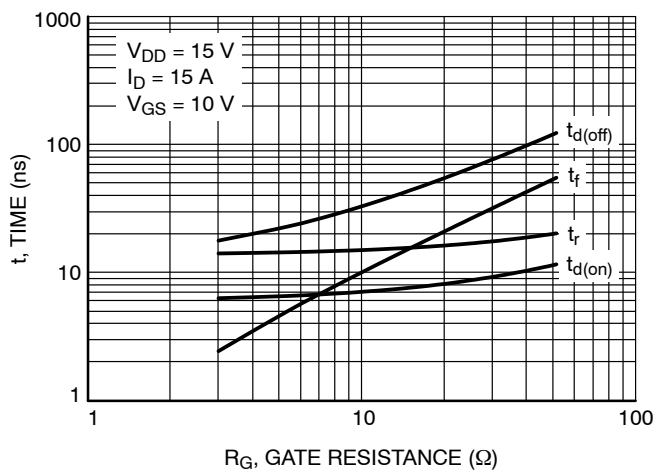


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

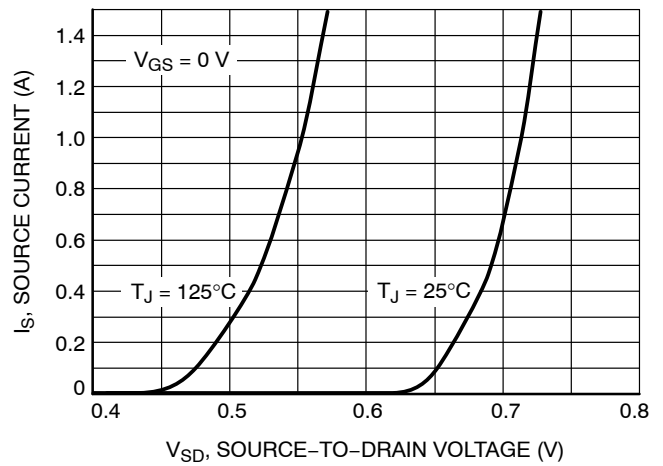


Figure 10. Diode Forward Voltage vs. Current

NTLUS4C12N

TYPICAL CHARACTERISTICS

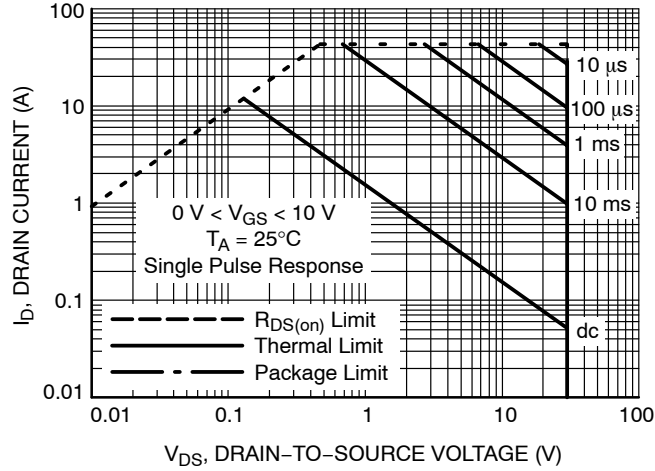


Figure 11. Maximum Rated Forward Biased Safe Operating Area

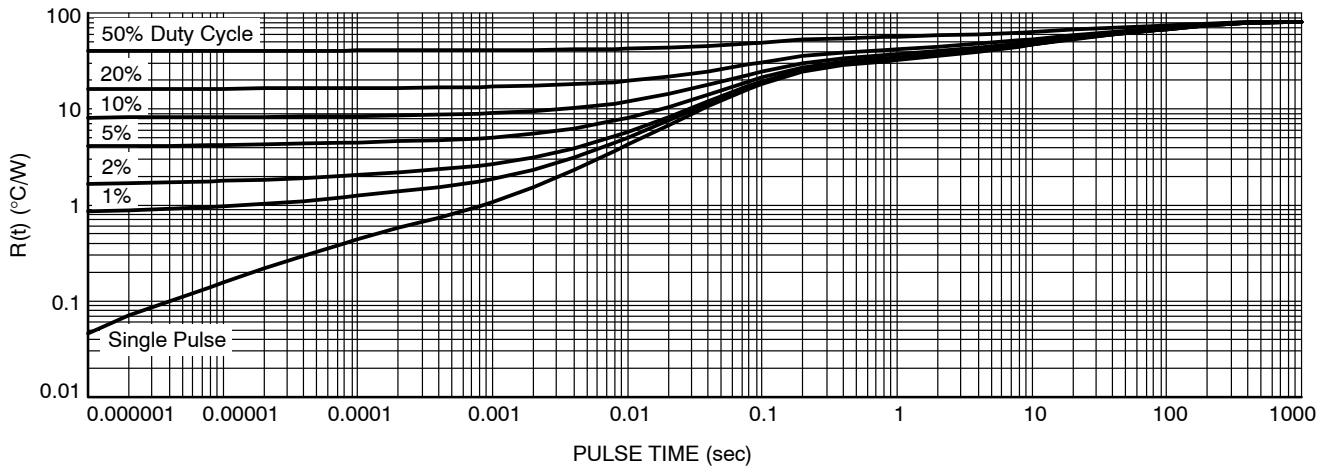


Figure 12. Thermal Response

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLUS4C12NTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS4C12NTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

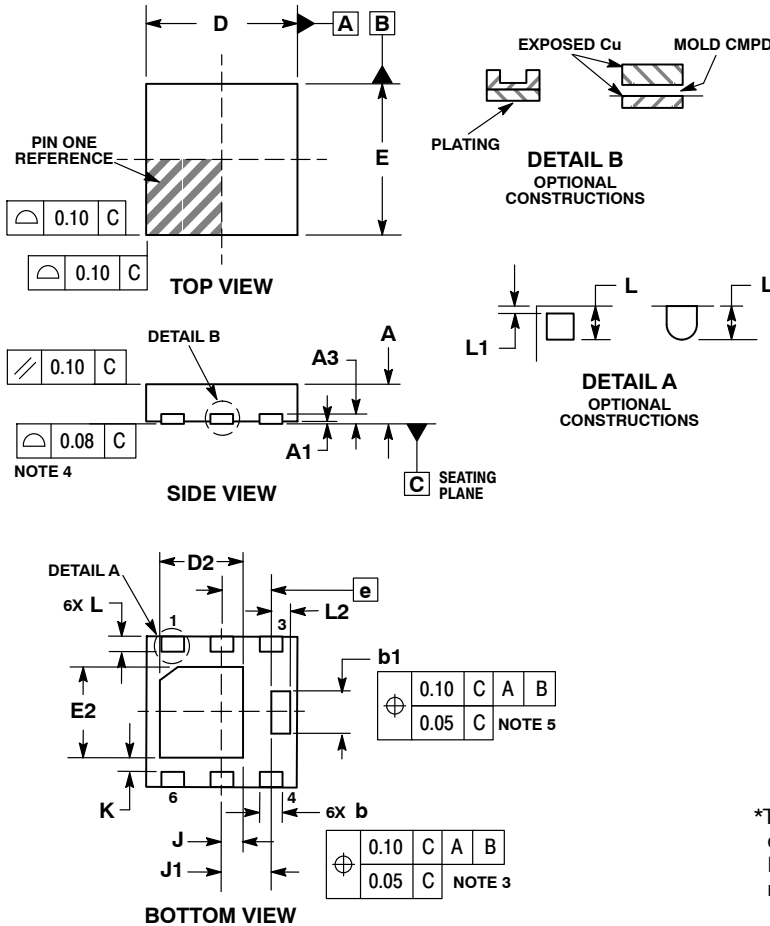
ON Semiconductor®



SCALE 4:1

UDFN6 2x2, 0.65P
CASE 517BG-01
ISSUE A

DATE 04 FEB 2010



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
1. CENTER TERMINAL LEAD IS OPTIONAL. CENTER TERMINAL IS CONNECTED TO TERMINAL LEAD # 4.
2. LEADS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.25	0.35
b1	0.51	0.61
D	2.00 BSC	
D2	1.00	1.20
E	2.00 BSC	
E2	1.10	1.30
e	0.65 BSC	
K	0.15 REF	
J	0.27 BSC	
J1	0.65 BSC	
L	0.20	0.30
L1	---	0.10
L2	0.20	0.30

GENERIC MARKING DIAGRAM*

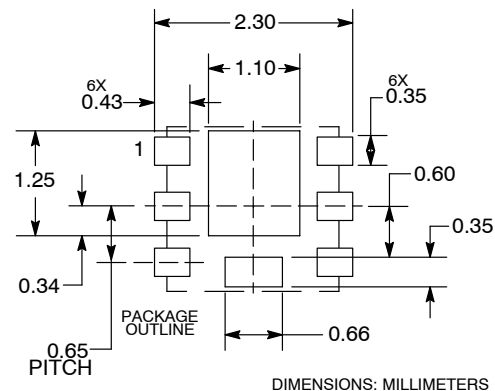


XX = Specific Device Code
M = Date Code

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT



DOCUMENT NUMBER:	98AON48158E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	UDFN6 2X2, 0.65P	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View NTLUS4C12NTAG on WIN SOURCE](#)

 [ON Semiconductor](#) Information

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management